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The invention relates to the semiconductor technique and may be used for semiconductor electronic materials obtaining .

The process for obtaining the multilayer epitaxial structures, including the successive epitaxial layers growing containing different components in the corresponding gas flow, after each layer growing, the latter one is enveloped by the inactive gas flow till the following layer growing.

The installation for obtaining the multilayer epitaxial structures includes reactor with chambers for layers growing, connected with the rod, substrates fixation unit, driving mechanism for growing chambers connected with the rod. Substrates fixation unit is realized in the form of shelves and is placed into the tubes, disposed one above another at a distance which doesn't exceed the minimum diffusion length of the used gas.

The technical result consists in providing the possibility of obtaining epitaxial multilayer structures having the sharp profile.

Claims: 2

Fig.: 4